



PHPT60410NY

40 V, 10 A NPN high power bipolar transistor

27 January 2015

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60410PY

2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

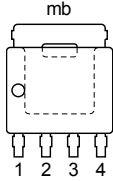
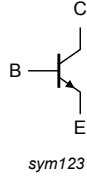
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I_C	collector current		-	-	10	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	20	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 10$ A; $I_B = 1$ A; pulsed; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_{amb} = 25$ °C	-	28	40	m Ω



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p>LFPAK56; Power-SO8 (SOT669)</p>	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT60410NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60410NY	0410NAB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

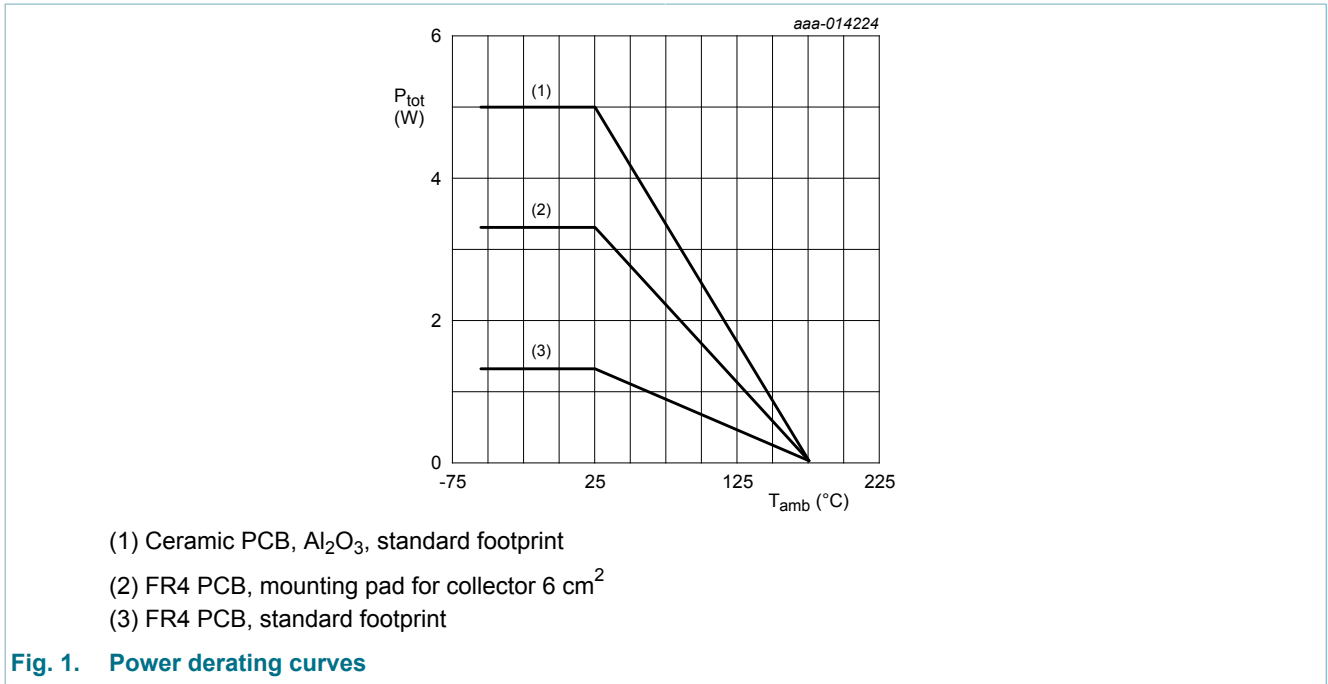
Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	40	V
V_{CEO}	collector-emitter voltage	open base		-	40	V
V_{EBO}	emitter-base voltage	open collector		-	7	V
I_C	collector current			-	10	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	20	A
I_B	base current			-	1	A
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms		-	2	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
T_j	junction temperature			-	175	°C
T_{amb}	ambient temperature			-55	175	°C
T_{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².

[3] Device mounted on an ceramic PCB; Al₂O₃, standard footprint.

[4] Power dissipation from junction to mounting base.



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	45	K/W
			[3]	-	-	30	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	-	6	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

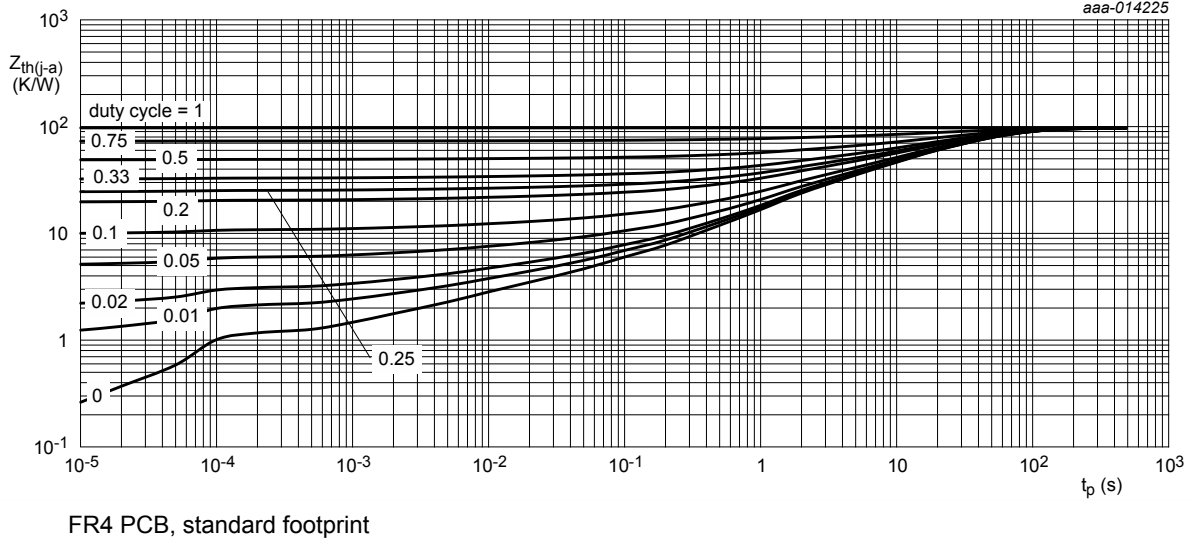


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

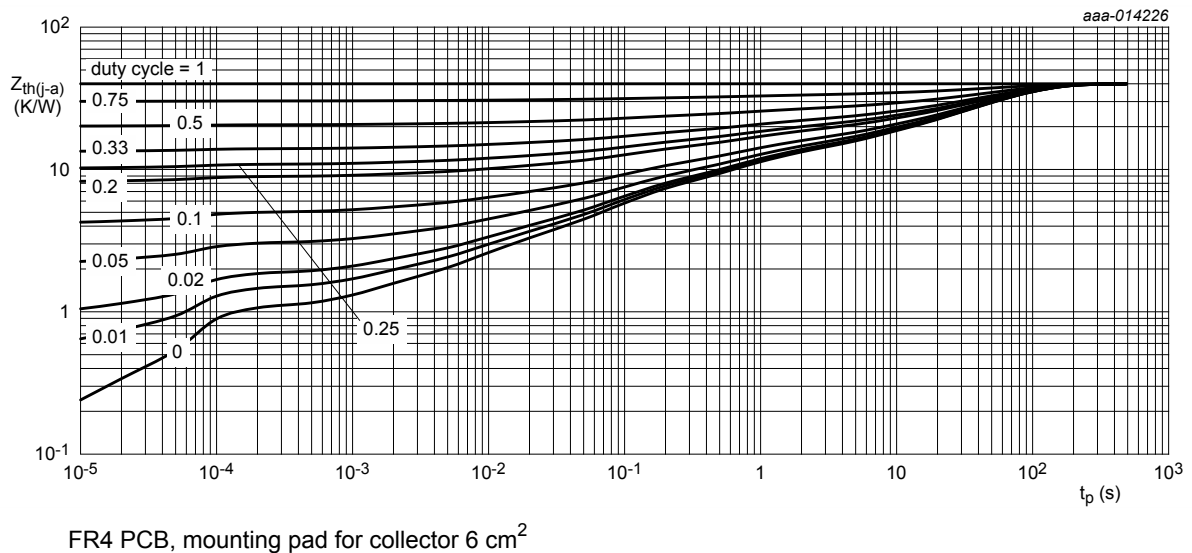


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = 32 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
		V _{CB} = 32 V; I _E = 0 A; T _j = 150 °C	-	-	50	µA
I _{CES}	collector-emitter cut-off current	V _{CE} = 32 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	230	370	-	

40 V, 10 A NPN high power bipolar transistor

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	220	360	-	
		$V_{CE} = 2\text{ V}; I_C = 5\text{ A}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	140	230	-	
		$V_{CE} = 2\text{ V}; I_C = 10\text{ A}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}; \text{pulsed}$	55	90	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 50\text{ mA}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}; \text{pulsed}$	-	35	50	mV
		$I_C = 5\text{ A}; I_B = 500\text{ mA}; \text{pulsed}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	140	200	mV
		$I_C = 10\text{ A}; I_B = 500\text{ mA}; \text{pulsed}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	330	460	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 10\text{ A}; I_B = 1\text{ A}; \text{pulsed}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	28	40	m Ω
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{pulsed}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	0.95	V
		$I_C = 5\text{ A}; I_B = 500\text{ mA}; \text{pulsed}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	1.2	V
		$I_C = 10\text{ A}; I_B = 500\text{ mA}; \text{pulsed}; t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	1.3	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	0.8	V
t_d	delay time	$V_{CC} = 12.5\text{ V}; I_C = 5\text{ A}; I_{Bon} = 250\text{ mA}; I_{Boff} = -250\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}$	-	15	-	ns
t_r	rise time		-	130	-	ns
t_{on}	turn-on time		-	145	-	ns
t_s	storage time		-	310	-	ns
t_f	fall time		-	95	-	ns
t_{off}	turn-off time		-	405	-	ns
f_T	transition frequency		$V_{CE} = 10\text{ V}; I_C = 500\text{ mA}; f = 100\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	128	-
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A}; f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	57	-	pF

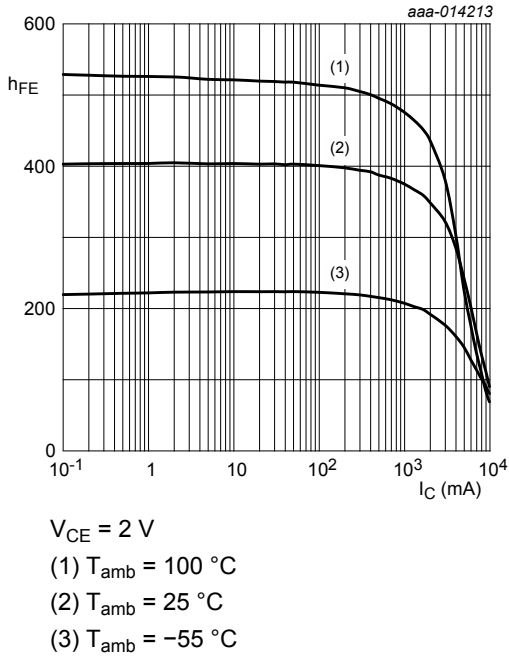


Fig. 4. DC current gain as a function of collector current; typical values

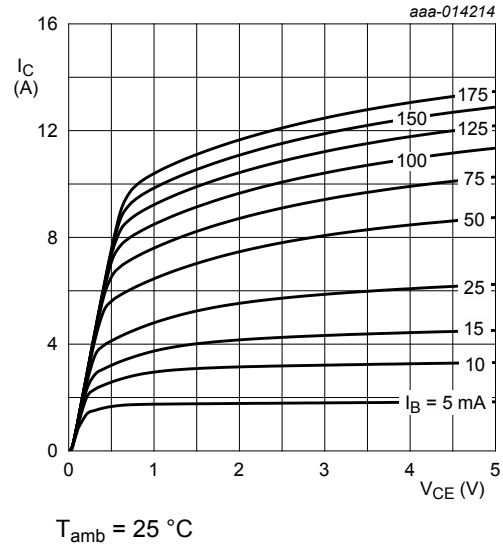


Fig. 5. Collector current as a function of collector-emitter voltage; typical values

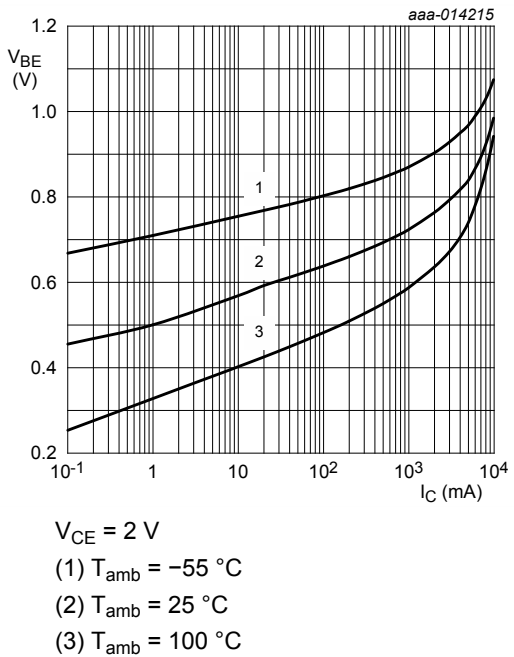


Fig. 6. Base-emitter voltage as a function of collector current; typical values

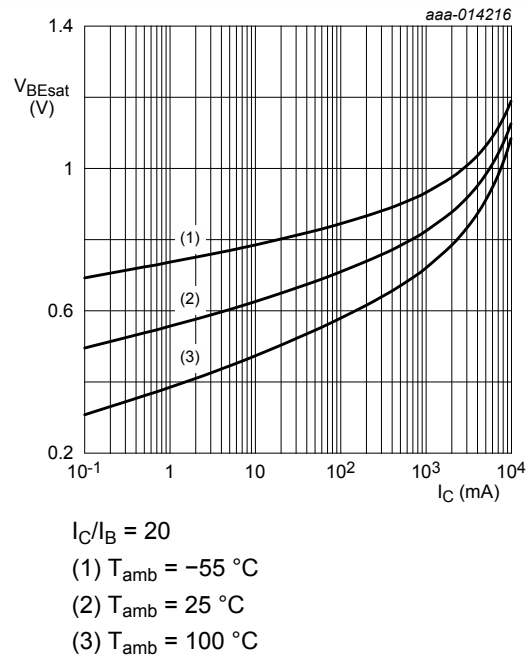
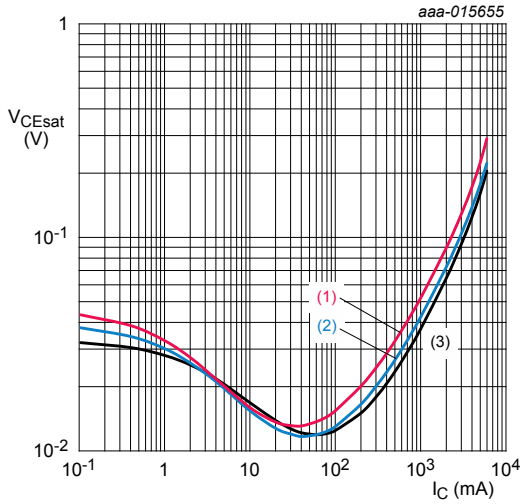
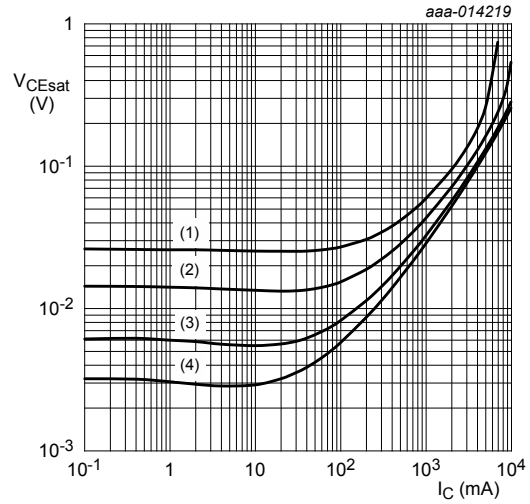


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



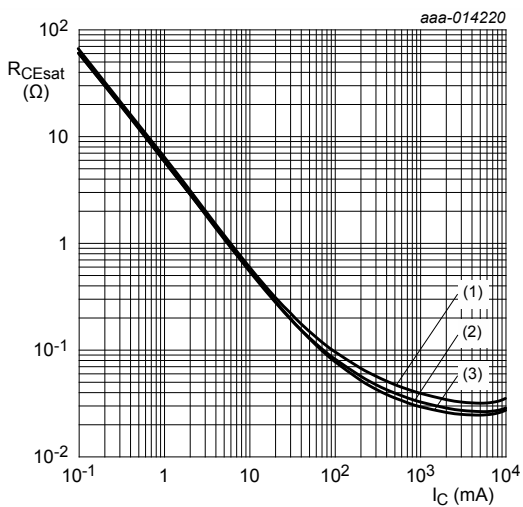
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



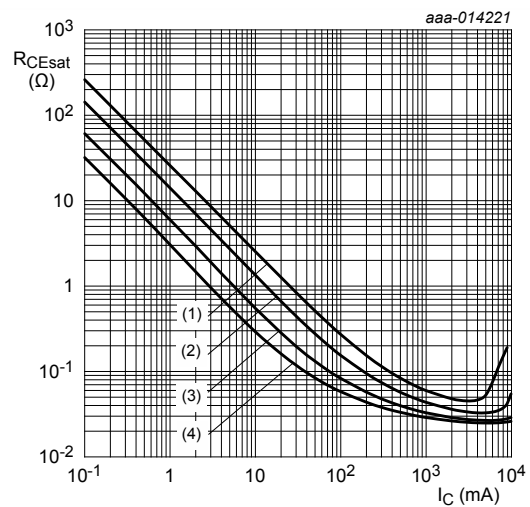
$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 20$
 (4) $I_C/I_B = 10$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 20$
 (4) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

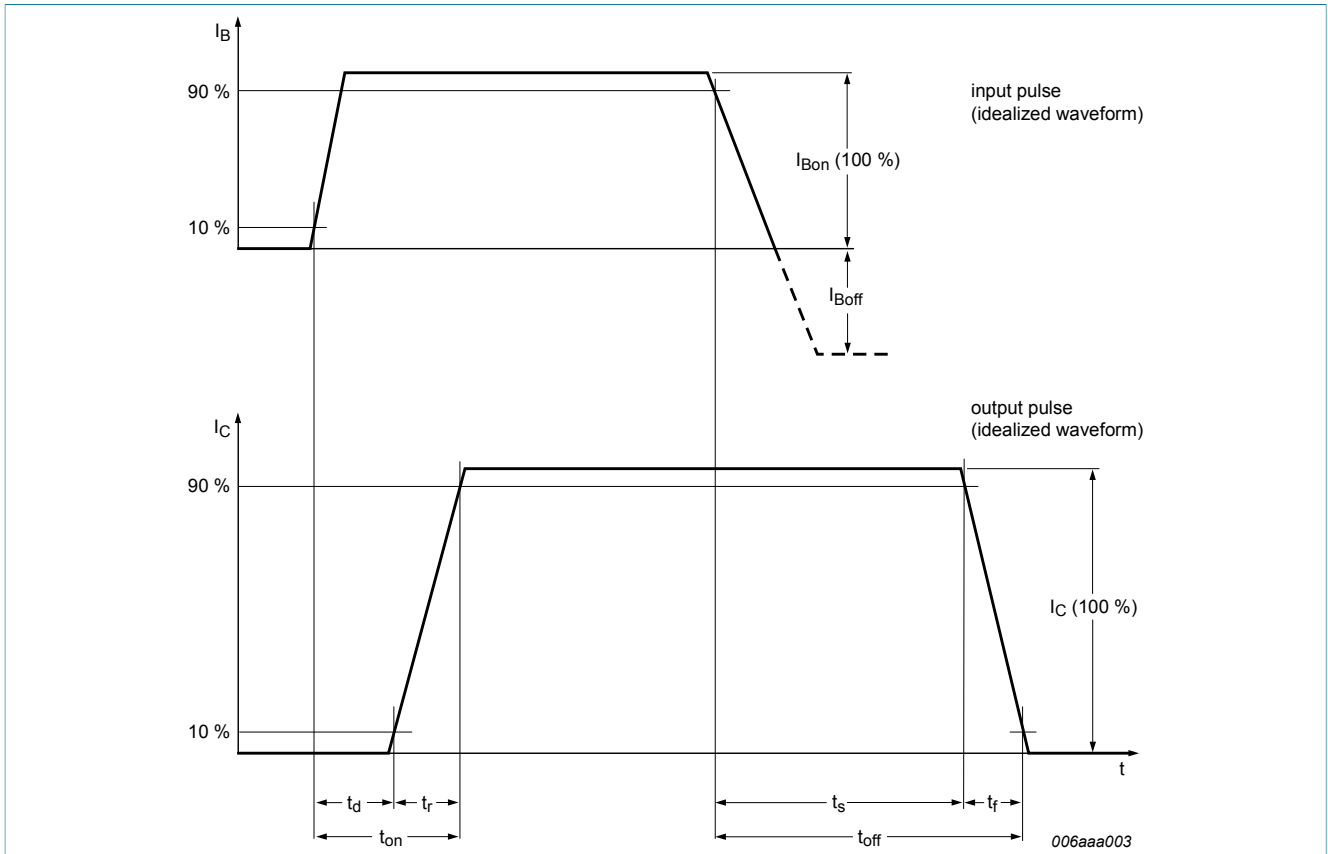


Fig. 12. BISS transistor switching time definition

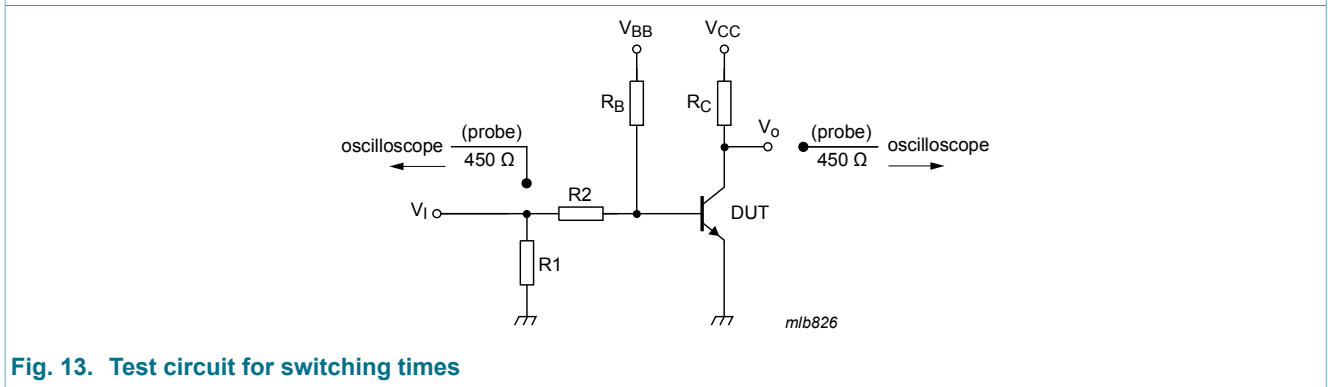


Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

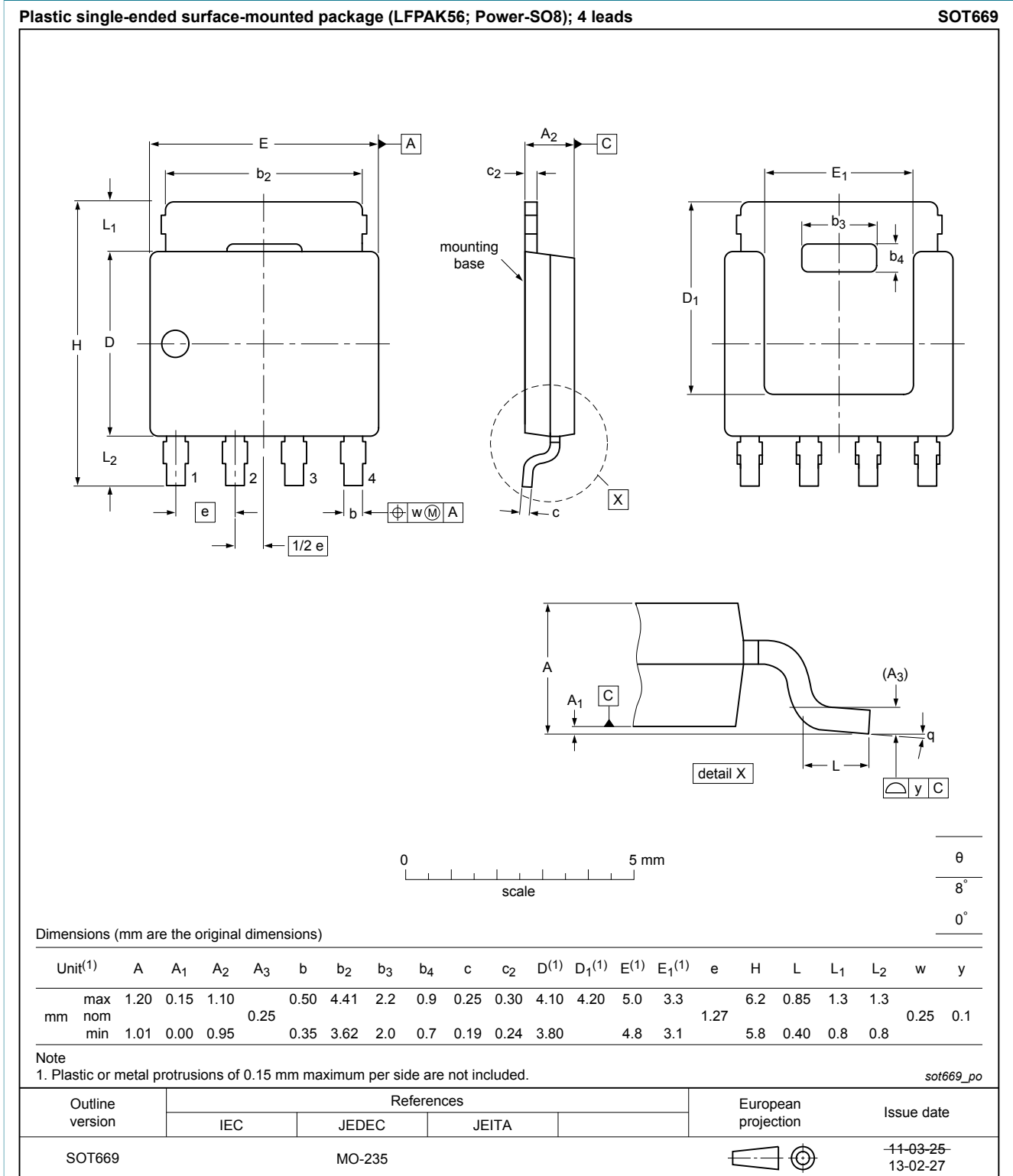


Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

13. Soldering

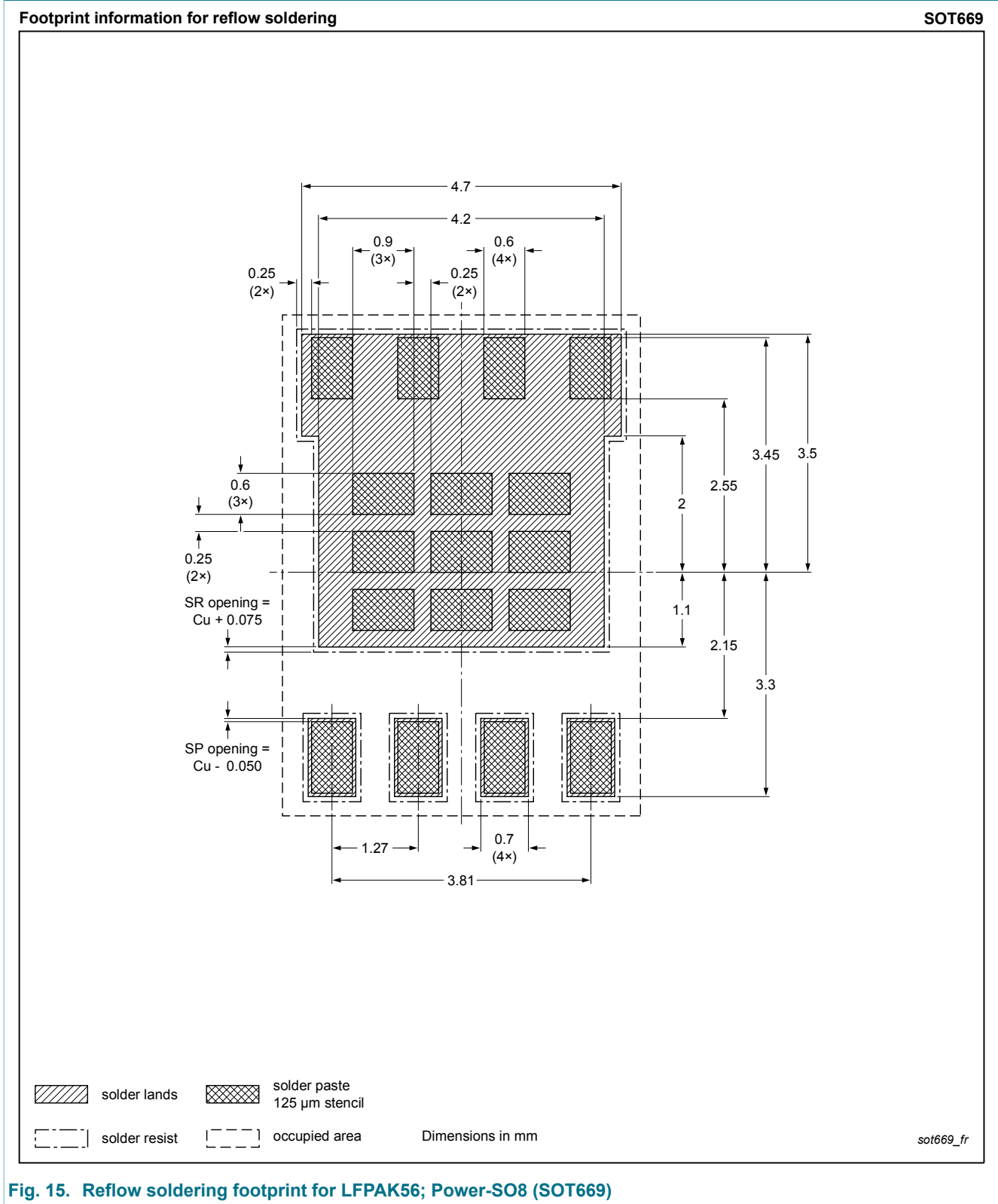


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60410NY v.1	20150127	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	9
11.1	Quality information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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